

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)**AUTHOR INDEX**

- Abelson, J.R., A27.3
 Aberle, Armin G., A5.11
 Agarwal, Sumit, A1.1
 Águas, H., A9.6, A26.6
 Ahmed, Haroon, A16.2
 Alpuim, P., A18.6
 Amaral, A., A22.5
 An, C.P., A3.4
 Andoh, Nobuyuki, A6.2, A6.10
 Andrade, Adnei M., A23.5
 Ang, T.C., A8.5
 Arai, Kenta, A20.6
 Arsenault, L.-F., A14.3
 Arya, R.R., A11.4
 Asada, Katsumi, A16.3
 Atwater, Harry A., A1.3, A3.2
 Aydil, Eray S., A1.1

 Badran, Rashad I., A23.7
 Bae, Sanghoon, A26.1
 Bailat, J., A15.3
 Balberg, I., A22.2
 Banerjee, A., A15.1
 Banerji, N., A8.7
 Barkema, G.T., A28.1
 Baugh, Jonathan, A19.1, A27.4
 Belich, T.J., A14.5
 Bender, Hugo, A8.8
 Bennett, M., A11.4
 Bent, Stacey F., A3.1
 Bergmann, Ralf B., A22.3
 Beserman, Robert, A8.3, A25.5
 Beyer, Wolfhard, A3.3, A9.2, A13.1, A25.5
 Birkholz, Mario, A15.4
 Birmans, Franz, A19.6
 Biswas, Parthapratim, A28.1
 Biswas, R., A14.1
 Boucinha, M., A26.4
 Boyce, J.B., A18.4
 Brammer, Torsten, A19.6
 Branz, Howard M., A12.2, A13.3, A28.2
 Braunstein, R., A8.4, A23.4
 Braz Fernandes, F., A7.6
 Brechtel, H., A5.5
 Brogueira, P., A22.5

 Cabrita, A., A9.6
 Capangpangan, R., A15.1
 Caputo, D., A26.3
 Carius, R., A15.2, A26.5
 Carlson, D.E., A11.4, A12.3, A25.4
 Caymax, Matty, A8.8
 Chack, Albert, A25.5
 Chae, Yongkee, A4.4
 Chandrashekar, D., A3.6
 Chaudhuri, P., A23.1
 Chen, Chi, A24.6
 Chen, Wangchun, A27.3
 Cheng, C.F., A6.4
 Cheng, I-Chun, A26.1
 Cheong, Hyeonsik M., A28.5
 Cho, N.-H., A23.3
 Choi, Duck-Kyun, A6.8
 Chu, V., A18.6, A24.5, A26.4
 Cohen, J. David, A12.5, A25.3
 Collins, Robert W., A5.4, A12.3, A16.4, A24.6
 Conde, J.P., A18.6, A24.5, A26.4
 Crandall, Richard S., A19.2, A27.2, A28.2
 Crucet, R., A15.1

 Dalal, Vikram L., A5.2, A5.3, A8.4, A25.12
 Dasgupta, A., A25.8
 de Cesare, G., A26.3
 Deb, Sayten K., A28.5
 deFreese, Matt, A5.2
 de Lima, A.P., A22.5
 DeLong, M.C., A3.4
 Dentel, Didier, A8.8
 Dettmer, Klauss, A8.3
 Dexheimer, S.L., A16.5
 Dillon, A.C., A7.2
 Dirani, Ely A.T., A23.5
 Dloczik, L., A24.5
 Duan, H.L., A3.1
 Duarte Naia, M., A22.5
 Dubail, S., A15.3
 Dubcek, Pavo, A19.9
 Durrani, Zahid A.K., A16.2
 Dusane, Rajiv O., A3.6
 Dutta, J., A6.9
 Dutta Gupta, N., A23.1

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- Eccleston, Bill, A26.2
 Edelman, Felix, A25.5
 Eguchi, Keisuke, A4.4
 Ehara, Takashi, A20.4
 Eshed, Anat, A8.3
 Falter, Julie, A5.2
 Fantoni, A., A25.11
 Faro, E., A8.7
 Faÿ, S., A15.3
 Fedders, P.A., A3.5, A13.2, A19.4
 Fejfar, Antonín, A16.1
 Fenske, F., A5.7
 Ferlauto, Andre S., A5.4, A16.4, A24.6
 Fernandes, M., A18.5, A25.10, A25.11
 Ferreira, Gelio M., A24.6
 Ferreira, I., A7.6, A9.6, A26.7
 Figueiredo, J., A26.6
 Finger, F., A15.2, A25.8
 Flewitt, Andrew J., A6.7
 Fojtík, Petr, A16.1
 Fonash, Stephen J., A26.1
 Fonseca, Fernando J., A23.5
 Fonseca, L.F., A22.2
 Fortmann, C.M., A12.6, A19.5
 Fortunato, E., A7.6, A9.6, A26.6,
 A26.7
 Fuhs, Walther, A5.7, A15.4
 Fujiwara, Hiroyuki, A1.2
 Furuta, Yoshikazu, A16.2
 Ganguly, Gautam, A11.4, A12.3,
 A25.3, A25.4
 Gaspar, J., A26.4
 Gedvilas, L.M., A3.3, A7.2
 Gemmer, Christian, A25.9
 Gerbi, Jennifer E., A27.3
 Gibson, J. Murray, A27.3
 Gleaton, M., A11.4
 Gleskova, H., A19.7
 Gloeckner, J., A25.10
 Goddard III, W.A., A3.2
 Goodwin, David G., A3.2
 Gordo, P.M., A22.5
 Goryll, Michael, A8.8
 Gracin, D., A6.9
 Gueorguieva, Mariana J., A19.3, A22.6
 Guha, Subhendu, A7.5, A9.7, A11.3,
 A12.5, A19.2, A25.2
 Gutierrez, J.J., A3.4
 Haji, Saber, A6.5, A6.6
 Hamers, E.A.G., A4.2
 Hamma, S., A9.5
 Han, Daxing, A7.4, A9.7, A19.1, A27.4
 Han, Min-Koo, A6.11
 Harder, Nils-Peter, A5.11
 Hartman, Z., A15.6
 Hata, N., A12.6, A19.5
 Hazra, S., A9.5
 Heath, Jennifer, A12.5, A25.3
 Heck, Stephan, A12.2
 Herberg, J., A3.5
 Herrold, Jason T., A25.12
 Herzog, P.G., A18.2
 Heuser, Brent J., A27.3
 Ho, J., A17.4, A18.1, A18.4
 Hoefnagels, J.P.M., A4.2
 Holt, Jason K., A1.3, A3.2
 Hong, J., A8.6
 Houben, L., A15.2
 Inglefield, C.E., A3.4
 Itoh, Hiroshi, A10.4
 Iwaniczko, Eugene, A3.3, A7.5
 Iyer, Suman B., A25.3
 Izmajlowicz, Marek A.T., A6.7
 Izu, M., A15.1
 Izumi, Akira, A4.5
 Jimenez Zambrano, R., A15.6
 Jones, S.J., A15.1
 Kakalios, J., A14.5
 Kamei, Toshihiro, A10.1
 Kamesaki, Koji, A4.5
 Kamiya, Toshio, A16.2
 Kaneko, Yoshiyasu, A16.3
 Kawashima, Yuji, A14.6
 Kessels, W.M.M., A1.1, A4.2, A8.6
 Khakifirooz, Ali, A6.5, A6.6
 Kim, Cheon-Hong, A6.11
 Kim, Chul-Ho, A6.8
 Kim, Hyoung-June, A5.8
 Kiyama, Seichi, A11.1
 Kleinhammes, Alfred, A27.4
 Knipp, D., A18.2
 Koch, Christian, A16.1

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- Kocka, Jan, A16.1
 Koga, Kazunori, A5.6
 Kondo, Michio, A1.2, A4.3, A12.1,
 A14.2, A15.5
 Könenkamp, R., A24.5
 Koob, Markus, A3.6
 Korevaar, B.A., A24.4
 Kottwitz, A., A5.5
 Koval, Randy J., A5.4, A12.3, A16.4
 Krause, Mathias, A19.6, A26.5
 Kroll, U., A15.3
 Kumeda, Minoru, A10.4, A14.6
 Kunst, Marinus, A23.2, A24.1
 Kuske, J., A5.5
 Kwon, Do-Hyun, A5.8
 Kwon, Se-Youl, A6.8

 Lambertz, A., A25.8
 Lau, R., A17.4, A18.1, A18.4
 Lauinger, T., A8.6
 Lavareda, G., A22.5
 Lebib, S., A14.3
 Lee, Jae-Bok, A6.8
 Lee, Se-Hee, A28.5
 Lee, Wook Jae, A25.7
 Lemmi, F., A18.1, A26.3
 Leopold, D.J., A3.5
 Leung, T.C., A6.4
 Ligatchev, Valeri, A9.8
 Lim, Dong Gun, A25.7
 Lim, E.H., A8.5
 Lin, G., A11.4, A25.4
 Lin, Shu-Ya, A21.5
 Liu, H., A8.5
 Löffler, J., A15.6
 Longeaud, C., A9.5, A14.4, A23.1
 Loo, Roger, A8.8
 Lopes Gil, C., A22.5
 Lord, Kenneth, A7.5, A9.7, A25.2
 Louro, P., A18.5, A25.10, A25.11
 Lu, J.P., A17.4, A18.1, A18.4
 Lubianiker, Yoram, A25.3
 Luysberg, M., A15.2

 Madan, A., A3.4
 Mahan, A. Harv, A3.3, A7.2, A28.2
 Main, Charlie, A19.3, A22.6, A23.7
 Maroudas, Dimitrios, A1.1
 Marra, Denise C., A1.1

 Martins, R., A7.6, A9.6, A26.6, A26.7
 Maruyama, Arata, A20.4
 Maruyama, Eiji, A11.1
 Mascarenhas, Angelo, A28.5
 Masuda, Atsushi, A4.5
 Mates, Tomás, A16.1
 Matsuda, Akihisa, A1.2, A4.3, A10.1,
 A12.1, A12.6, A14.2, A15.5,
 A19.5
 Matsumura, Hideki, A4.5
 Matusiak, R., A17.4
 Meaudre, M., A23.1
 Meaudre, R., A23.1
 Meier, J., A15.3
 Metselaar, Wim, A25.1
 Meunier-Beillard, Philippe, A8.8
 Middya, A.R., A9.5, A25.6
 Milat, Ognjen, A19.9
 Milne, William I., A6.7
 Min, Robert B., A17.5
 Mizuta, Hiroshi, A16.2
 Mohajerzadeh, Shamsoddin, A6.5,
 A6.6
 Morigaki, Kazuo, A12.4
 Morrison, Neil A., A6.7
 Morrison, S., A3.4
 Moschner, J.D., A8.6
 Mousseau, Normand, A28.1
 Muccillo, Reginaldo, A23.5
 Mukherjee, Chandrachur, A3.6, A25.6
 Mulato, M., A18.1, A18.4
 Muller, R.P., A3.2
 Myers, K.E., A16.5

 Naeli, Kianoush, A6.6
 Nardes, Alexandre M., A23.5
 Nascetti, A., A26.3
 Nasuno, Y., A4.3, A15.5
 Nelson, Brent P., A3.3, A23.4, A28.2,
 A28.5
 Nemanich, R.J., A6.9
 Nerding, Melanie, A22.3
 Nguyen, Hien V., A24.6
 Nickel, N.H., A28.3
 Nishiguchi, Katsuhiko, A20.6
 Niu, X., A12.3
 Norberg, R.E., A3.5
 Nunes, P., A26.6
 Nunes de Carvalho, C., A22.5

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- Oberbeck, Lars, A22.3
 Oda, Shunri, A20.6
 Oelting, Stefan, A5.11
 Ogihara, Chisato, A12.4
 Ohno, Hiromasa, A4.4
 Okamoto, Shingo, A11.1
 Omachi, Junichi, A20.6
 Owens, Jessica M., A7.4, A9.7
- Palinginis, Kimon C., A12.5
 Palma, F., A26.3
 Pan, B.C., A14.1
 Park, M.-B., A23.3
 Park, Sung-Gye, A5.8
 Pearce, J.M., A12.3, A16.4
 Perkins, J.D., A3.3, A7.2
 Pivac, Branko, A19.9
 Poon, M.C., A6.4
 Pratim Ray, P., A23.1
- Rakel, M., A28.3
 Rakhlin, M., A2.1
 Ramalingam, Shyam, A1.1
 Rath, J.K., A15.6
 Ray, S., A9.5
 Ready, S.E., A17.4, A18.4
 Rech, Bernd, A25.5
 Reedy, Robert C., A28.2
 Reinig, P., A5.7
 Reynolds, Steve, A19.3, A22.6, A23.7
 Rezaee, Leila, A6.5
 Rezek, Bohuslav, A16.1
 Robertson, J., A1.5
 Roca, F., A26.3
 Rojahn, M., A2.1
 Roschek, Tobias, A25.5
 Rovira, Pablo I., A24.6
 Roy, D., A14.4, A23.1
 Ryu, Se-won, A5.8
- Sacher, E., A14.3
 Sameshima, Toshiyuki, A6.2, A6.3,
 A6.10, A16.3
 Saviot, L., A23.1
 Scholten, C., A15.2
 Schram, D.C., A8.6, A24.4
 Schroeder, Bernd, A3.6, A7.3, A25.6
 Schropp, Ruud E.I., A3.5, A11.2,
 A15.6, A17.3
- Schubert, Markus B., A2.1, A18.5,
 A25.9, A25.10
 Schwarz, R., A18.5, A25.10, A25.11
 Sedghi, Naser, A26.2
 Selle, Burkhardt, A5.7, A15.4
 Serra, J., A8.7
 Shah, A., A15.3
 Sheng, S.R., A8.4, A23.4
 Shimizu, S., A14.2
 Shimizu, Satoshi, A12.1
 Shimizu, Tatsuo, A10.4, A14.6
 Shinohara, Wataru, A11.1
 Shiratani, Masaharu, A5.6
 Shitakata, Norio, A10.4
 Silva, R., A26.6
 Silva, V., A9.6, A26.6
 Smeets, Jozef, A11.3
 Smets, A.H.M., A4.2, A22.4
 Smit, C., A4.2, A24.4
 Soares, F., A26.6
 Soleimani, Ebrahim Asl, A6.5, A6.6
 Song, In-Hyuk, A6.11
 Sriraman, Saravanapriyan, A1.1
 Stannowski, B., A17.3
 Stephan, U., A5.5
 Stiebig, Helmut, A18.2, A19.6, A25.8,
 A26.5
 Stradins, Paul, A12.1, A14.2
 Street, R.A., A17.4, A18.1, A18.4
 Strunk, Horst P., A22.3
 Stuchlík, Jirí, A16.1
 Stuchliková, Ha, A16.1
 Subrahmanyam, V.S., A22.5
 Sudijono, J.L., A8.5
 Sunda-Meya, A., A6.9
 Suzuki, S., A4.3
 Svrcek, Vladimír, A16.1
 Swiatek, Maribeth, A1.3, A3.2
- Takahashi, Hiroyuki, A6.2
 Takano, Akihiro, A1.1
 Takemura, Hitoshi, A12.4
 Tan, Yong T., A16.2
 Tanaka, Makoto, A11.1
 Taylor, P.C., A3.4
 Terakawa, Akira, A11.1
 Terasa, R., A5.5
 Thiesen, J., A7.2
 Thiesen, Jack, A27.2

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001

Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- Thom, Wilhelm, A23.2
Treacy, Michael M.J., A27.3
Tsunoda, Yoshiyuki, A16.3
Tucci, M., A26.3
- Vallat-Sauvain, E., A15.3
van Assche, F.J.H., A8.6
van den Heuvel, Joost J.G., A25.1
Vandervorst, Wilfried, A8.8
Van Der Werf, C.H.M., A15.6
van de Sanden, M.C.M., A1.1, A4.2,
A8.6, A22.4, A24.4
Vanecek, M., A3.3
Vanhaeren, Danielle, A8.8
van Helden, J.H., A22.4
Van Schuylenbergh, K., A18.4
van Swaaij, René A.C.M.M., A24.4,
A25.1
van Veen, Marieke K., A11.2, A15.6,
A17.3
Van Veenendaal, P.A.T.T., A15.6
Vassiliev, V.Y., A8.5
Vescan, Lili, A8.8
Vetterl, O., A15.2, A25.8
Vieira, M., A18.5, A25.10, A25.11
Vignoli, S., A23.1
Vilarinho, P., A7.6
Vink, R.L.C., A28.1
Vlahovic, B., A6.9
von Aichberger, Susanne, A23.2, A24.1
Voyles, Paul M., A27.3
Vygranenko, Yu., A18.5, A25.10
- Wada, Takehito, A10.1
Wagner, Heribert, A19.6, A25.8, A26.5
Wagner, Sigurd, A17.2, A17.5, A19.7,
A26.1
Wagner, Thomas A., A22.3
- Wang, C.Y., A8.5
Wang, Qi, A7.4, A7.5, A16.5
Watakabe, Hajime, A6.3
Watanabe, Tadashi, A6.3, A6.10
Watanabe, Yukio, A5.6
Weber, Urban, A3.6, A7.3, A25.6
Weil, Raoul, A25.5
Weinberg-Wolf, Jennifer, A7.4, A9.7
Weisz, S.Z., A22.2
Werner, Peter, A25.5
White, S.D., A17.4
Williamson, Don L., A3.3, A7.2, A15.4
Wong, W.S., A17.4
Wronski, Christopher R., A5.4, A12.3,
A16.4, A24.6
Wu, Ming, A17.2
Wu, Yue, A27.4
Wünsch, Frank, A23.2, A24.1
- Xu, Yueqin, A3.3, A7.4, A23.4, A28.2
- Yan, Baojie, A9.7, A11.3, A25.2
Yang, Jeffrey C., A7.5, A9.7, A11.3,
A12.5, A19.2, A25.2
Ye, Y., A14.1
Yelon, A., A14.3
Yi, Junsin, A25.7
Yoo, Juhn-Suk, A6.11
Yoon, Jong-Hwan, A23.6
Yoshida, Toyonobu, A4.4
Yue, Guozhen, A7.4, A9.7
- Zaharias, G.A., A3.1
Zeman, Miro, A25.1
Zhang, S.B., A13.3
Zheng, J.Z., A8.5
Zulim, Ivan, A19.9

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001

Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)**SUBJECT INDEX**

- activation-relaxation technique,
 - A28.1
- a-germanium, A5.2
- alkylol group, A20.4
- amorphous, A16.4
 - and microcrystalline silicon, A26.4
 - hydrogenated silicon, A12.1
 - semiconductors, A23.7
 - Si, A5.3
 - silicon(-), A1.1, A3.1, A3.3, A5.3, A5.4, A5.5, A5.6, A6.5, A6.6, A6.9, A9.2, A11.1, A11.2, A11.3, A11.4, A12.3, A12.4, A13.1, A13.3, A14.1, A14.4, A14.5, A18.4, A19.2, A19.3, A19.5, A19.9, A20.4, A22.2, A22.6, A23.1, A23.2, A23.6, A25.2, A25.4, A25.9, A25.11, A27.3, A28.1, A28.2
 - carbon alloy, A3.6
 - nitride, A14.6
 - solar cell(s), A3.6, A7.3, A24.6
 - TFT, A17.4
- anisotropy, A27.4
- annealing(-), A25.2
 - induced Raman spectral changes, A14.3
- ArF-LCVD, A8.7
- argon dilution, A23.1
- a-SiGe:H, A7.5
- a-Si:H, A22.5, A24.4, A27.4
 - solar cells, A25.1
 - TFTs, A19.7
- atomic force microscopy, A3.4
- bandgap grading, A25.1
- capacitance measurement, A26.3
- capture coefficients of photocarriers,
 - A12.1
- carrier transport, A16.2
- catalytic chemical sputtering, A4.5
- cat-CVD, A1.3
- cavity ring down, A22.4
- challenges, A11.4
- charge transport, A16.1
- chemical
 - transport, A4.5
 - vapor deposition, A8.8
- CIGS, A25.9
- cluster, A5.6
 - Bethe lattice method, A21.5
- color sensor, A18.1, A18.2
- conductivity, A14.5
- confinement, A9.8
- conformal deposition, A24.5
- continuous random network, A28.1
- crystallization, A6.7, A6.9
- dangling bond(s), A13.2, A19.2
 - A19.4
- defect(s) A12.2, A12.5, A22.4 A22.5, A25.3
 - states, A16.3
- density of states, A22.6
- deposition, A8.3
 - rate, A3.3
- device simulation, A19.6
- diffusion, A8.3
- direct deposition, A17.5
 - simulation Monte Carlo, A3.2
- domain boundary, A19.1
- doped microcrystalline silicon, A18.6
- ECR plasma, A5.2
- effusion, A9.2
- electrical conductivity, A16.3
 - stability, A19.7
- electron
 - beam irradiation, A14.6
 - spin resonance, A10.4
 - transport properties, A8.4 A23.4
- electronic transport, A25.6
- electrostatic actuation, A26.4
- ellipsometry, A1.2
- Er-doped a-Si:H, A10.4
- ESR, A13.2, A19.4
- excimer laser annealing, A6.11
- expanding thermal plasma, A24.4
- femtosecond spectroscopy, A16.5

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- field(-), A6.7
 - aided lateral crystallization (FALC), A6.8
 - assisted metal-induced crystallization, A6.6
- fill factors, A25.3
- floating Si layer, A6.11
- fluctuation microscopy, A27.3
- free carrier optical absorption, A6.3
- gain, A26.3
- gas sensors, A26.7
- Ge islands, A8.8
- germanium carbide, A25.12
- grain, A6.11
 - boundary, A25.7
- growth, A1.5, A4.3
 - chemistry, A5.3
 - process, A4.2
 - simulation, A16.1
- Hall effect, A10.1
- heterojunctions, A24.1
- high(-)
 - deposition rate(s), A4.2, A8.6, A11.3, A23.4
 - growth rate, A7.4
 - rate, A15.1
 - solar cell, A7.5
- H₂O vapor
 - heat treatment, A6.3
 - treatment, A6.10
- homo-heterojunctions, A25.10
- hot wire, A3.3, A26.7
 - chemical vapor deposition (CVD), A1.3, A3.2, A3.6, A7.3, A7.5, A11.2, A15.6, A17.3, A25.6
 - deposition, A7.2
 - plasma assisted, A7.6
 - silicon, A3.5
- hydrogen, A3.5, A8.5, A14.4, A28.3
 - diffusion, A13.1, A27.2
 - dilution, A7.2, A7.3, A7.6, A9.7
 - plasma treatment, A6.10
- hydrogenated amorphous silicon (a-Si:H), A14.2, A19.1, A23.4, A26.2, A28.5
- illumination-induced Raman spectral changes, A14.3
- image
 - array, A18.1
 - sensor, A18.5
- impedance spectroscopy, A23.5
- ion-assisted deposition, A5.11
- IR/Raman intensity transfer, A14.3
- ITO, A25.7
- jet printing, A17.4
- Joule heating, A6.2
- junctions, A25.12
- kinetics, A12.3
- laser
 - crystallization, A16.3
 - crystallized silicon, A6.10
 - scanned photodiode, A18.5
- lateral
 - grain growth, A6.2
 - photo effect, A25.11
- light
 - induced
 - change, A19.5
 - defect(s), A12.3, A14.2
 - creation, A12.4
 - degradation, A12.1, A14.2
 - soaking, A14.6
- lineshape, A13.2, A19.4
- lithography, A17.4
- long-range hydrogen motion, A28.5
- low
 - bandgap amorphous (Ge, Si) alloys, A8.4
 - hydrogen, A5.8
 - temperature, A15.5
 - annealing, A25.4
 - crystalline silicon, A6.8
 - process, A5.8
- manufacturing, A11.4
- medium range order, A27.3
- mesh-type PECVD, A5.8
- metal-induced lateral crystallization, A6.6

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- metastability, A9.5, A12.5, A13.3, A14.1, A19.1, A28.3
- metastable defects, A19.3
- microcrystalline, A9.7, A16.4
 - germanium, A26.5
 - Si, A1.5, A10.1, A15.1, A15.2
 - silicon, A1.2, A3.4, A4.2, A4.3, A5.5, A15.5, A16.1, A19.6, A23.2, A23.5, A23.6, A25.5, A25.8, A28.3
 - thin film, A25.6
- microelectromechanical systems, A26.4
- microstructure, A9.2
- microwave, A15.1
- MILC, A6.4
- minority carrier properties, A22.3
- mobile-H, A28.2
- mobility, A23.2
 - gap, A16.4
 - lifetime product, A12.6
- modeling, A25.1
- molecular dynamics simulations, A1.1, A14.1
- morphology, A9.8
- MTPECVD, A26.6
- nanocrystalline silicon, A7.6, A16.5, A17.5, A26.1
 - thin films, A16.2
- nanomaterials, A9.6
- nanostructure, A20.6, A23.3
- nanowire, A16.2
- near infrared detector, A26.5
- Ni, A6.4
- nickel, A6.7
- NMR, A3.5
- noise, A23.7
- non-planar lithography, A2.1
- nucleation, A1.2, A1.3, A1.5
- numerical simulation, A25.11
- optical
 - emission, A5.2
 - properties, A8.4, A19.5
 - wave propagation, A18.2
- oxygen, A23.6
- PECVD, A9.6, A26.5
- phase change, A27.2
- phonon, A9.8
- photoconductivity, A12.2, A24.1
- photodiode, A18.1
- photoluminescence, A7.4, A10.4, A12.4, A20.6
- phototransistor, A26.3
- phototransport, A22.2
- photovoltaics, A2.1, A25.3
- piezoresistive sensors, A18.6
- pixel cross-talk, A18.4
- PL spectroscopy, A9.7
- plasma
 - CVD, A11.1
 - deposition, A5.3, A8.6, A25.12
 - enhanced chemical vapor deposition, A5.4, A9.5, A23.3
 - source, A5.5
- plastic substrate, A18.6, A19.7, A26.1
- polycrystalline silicon, A3.2, A6.2
- poly-Si, A6.4
 - on glass, A5.11
 - solar cell, A25.7
- polysilicon, A17.2
- porous silicon, A26.7
- position sensor, A26.6
 - beam spectroscopy, A22.5
- proton NMR, A27.4
- pseudopotential theory, A13.3
- quasimorphous silicon thin film, A9.5
- radicals detection, A3.1
- Raman
 - scattering, A28.5
 - spectroscopy, A3.4, A23.5
- real time spectroscopic ellipsometry, A5.4
- red-shift, A7.4
- reverse bias annealing, A25.4
- secondary ion mass spectrometry, A28.2
- sensitivity/resolution, A18.5
- sensitization, A22.2
- sensors, A18.4
- series resistance, A19.6

Cambridge University Press

978-1-107-41224-8 - Materials Research Society Symposium Proceedings: Volume 664:
Amorphous and Heterogeneous Silicon-Based Films—2001

Editors: Martin Stutzmann, James B. Boyce, J. David Cohen, Robert W. Collins
and Jun-ichi Hanna

Index

[More information](#)

- SiGe, A8.3
- silane plasma, A5.6
- silicon, A4.4, A4.5, A5.7, A5.11, A9.6,
A12.6, A15.3, A20.6, A23.3,
A24.5, A27.2
 - epitaxy, A22.3
 - germanium alloys, A12.5
 - nitride, A7.2, A8.6, A8.7, A17.3,
A21.5
 - thin film, A15.6
- SIMS, A8.5
- simulation, A25.9, A26.2
- SiN, A8.5
- single photon ionization, A3.1
- small angle x-ray scattering, A19.9
- solar cell(s), A4.3, A4.4, A5.7, A11.1,
A11.2, A15.2, A15.5, A19.2,
A24.4, A25.5, A25.8
- solid phase crystallization, A6.3
- solubility, A13.1
- space-charge limited current (SCLC),
A26.2
- spectral response, A25.10
- spectroscopic ellipsometry, A24.6
- sputtering, A5.7
- stability, A25.2
- Staebler-Wronski effect, A12.2
- steel substrate, A17.2
- structural
 - and optical properties, A8.8
 - properties, A15.4
- structure, A25.5
- subgap absorption, A12.6, A22.4
- substrate
 - orientation, A22.3
 - temperature, A25.8
- surface
 - infrared spectroscopy, A1.1
 - modification, A20.4
 - passivation, A24.1
- tandem solar cell, A15.6
- thermal annealing, A8.7
 - plasma CVD, A4.4
- thermopower, A14.5
- thin
 - film(s), A6.9, A24.5
 - detector, A18.2
 - transistor, A17.2, A17.3,
A17.5, A26.1
 - silicon films, A15.4
- transient photocurrent spectroscopy,
A19.3, A22.6
- transmission electron microscopy,
A15.2, A15.3
- transparent conductor oxide, A24.6
- transport
 - and structural properties, A23.1
 - simulation, A25.10
- trapping, A23.7
- UV, A6.5
- VHF, A11.3
- vibrational mode, A21.5
- voids, A14.4
- wire substrate, A2.1
- x-ray
 - diffraction, A10.1, A15.4
 - reflectance, A19.9
- zinc oxide, A15.3
- ZnO, A26.6